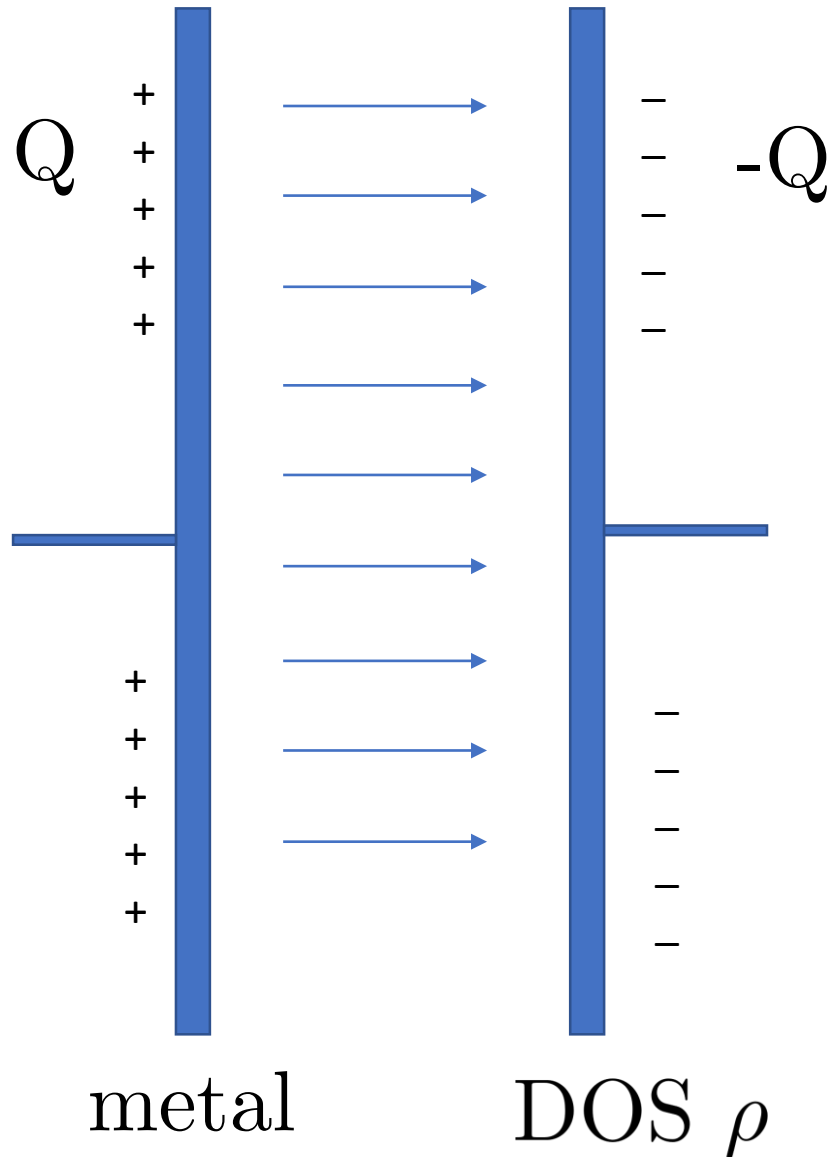


Quantum capacitance of quantum dots

RF seminar
17 June 2019

Quantum capacitance (finite DOS)



$$\Delta V_{\text{Galvani}} = \frac{Q}{C_{\text{geom}}}$$

$$\Delta\mu = \frac{Q}{e\rho} \longrightarrow \Delta V_{\text{quantum}} = \frac{Q}{e^2\rho}$$

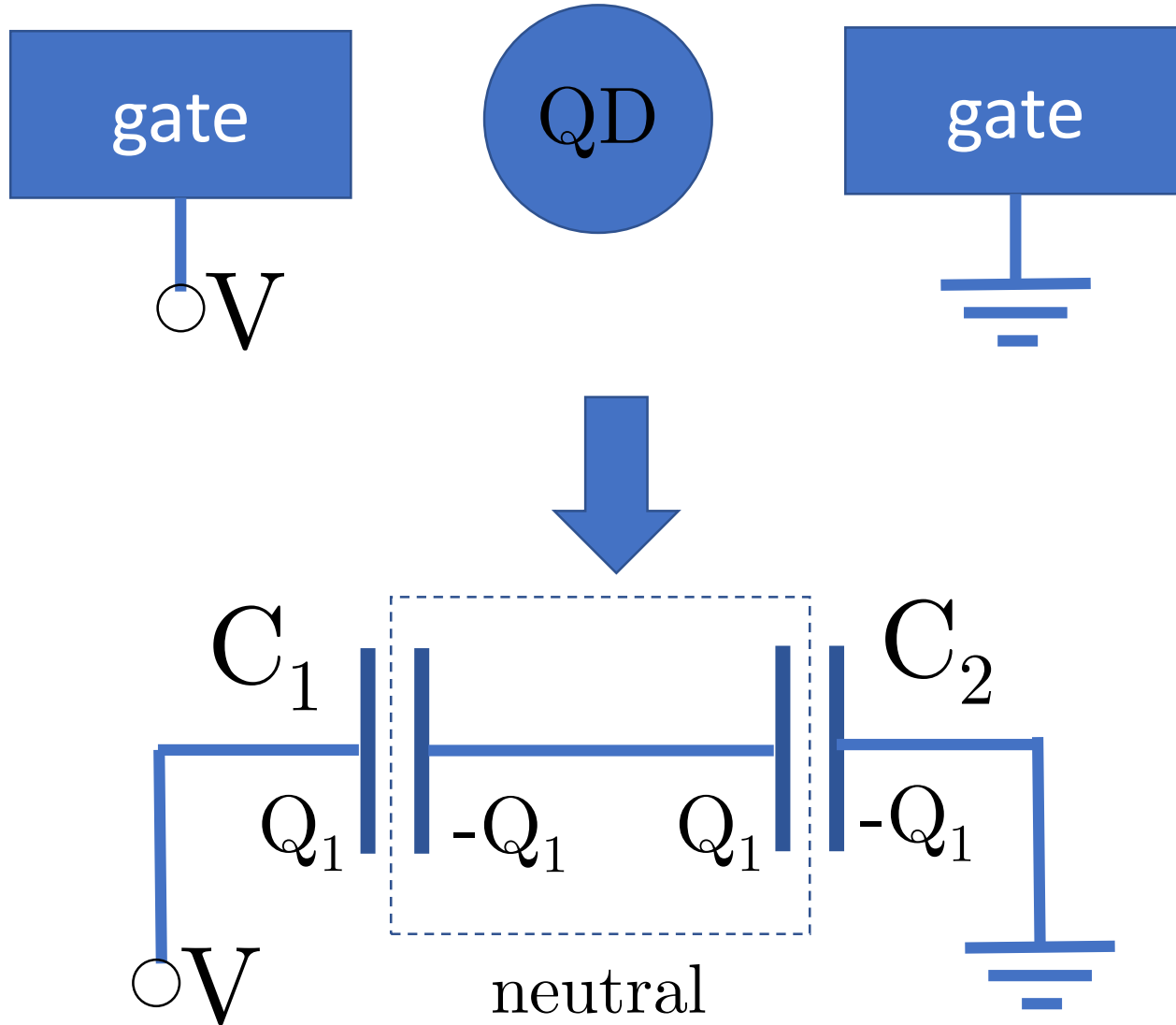
$$C_{\text{quantum}} = e^2\rho$$

$$\Delta V = Q \left(\frac{1}{C_{\text{geom}}} + \frac{1}{C_{\text{quantum}}} \right)$$

In series

More details: previous talk, Makk Péter

Geometrical capacitance

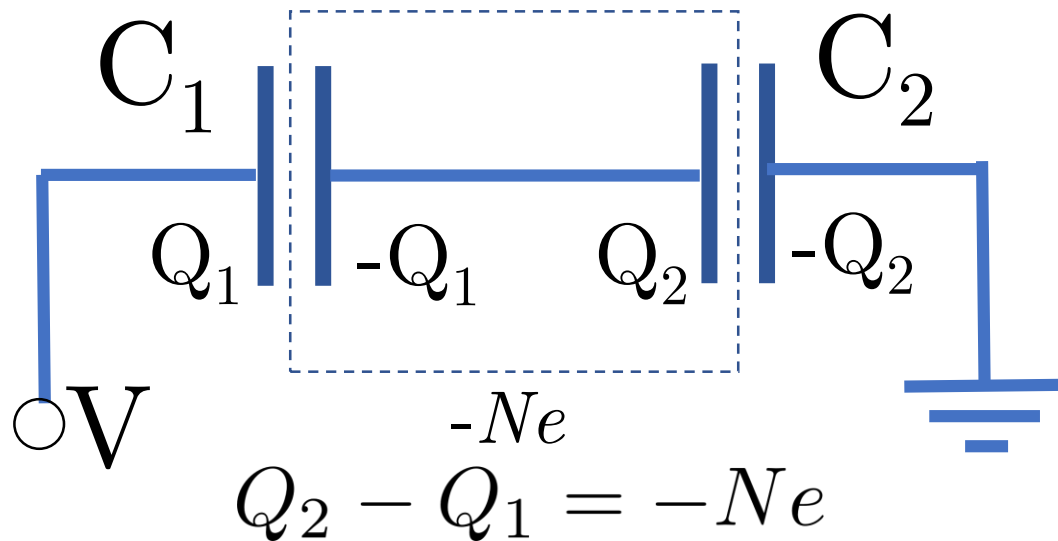
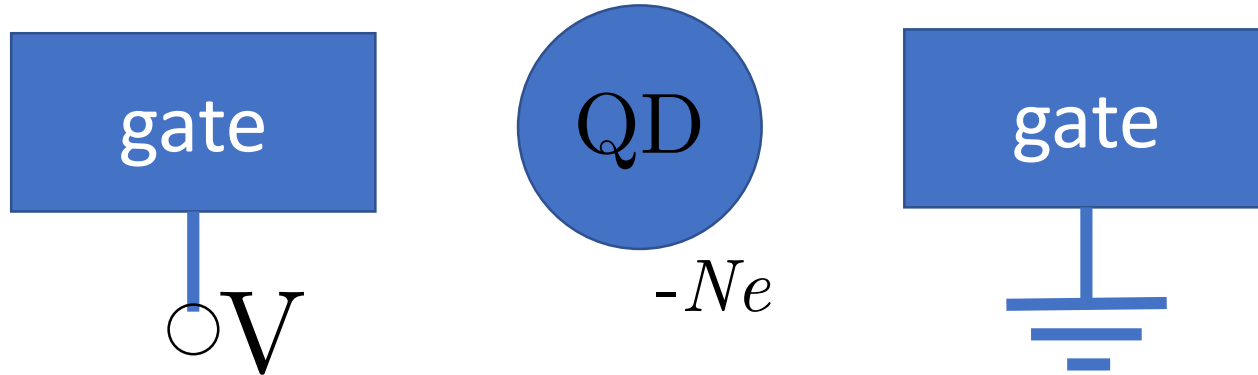


$$Q_1 \left(\underbrace{\frac{1}{C_1} + \frac{1}{C_2}}_{\frac{1}{C_g}} \right) = V$$

capacitors in series

$$V_{\text{dot}} = \frac{C_g}{C_2} V$$

Differential capacitance



$$\frac{Q_1}{C_1} + \frac{Q_2}{C_2} = V$$



$$Q_1 = C_g V + \frac{C_g}{C_2} Ne$$

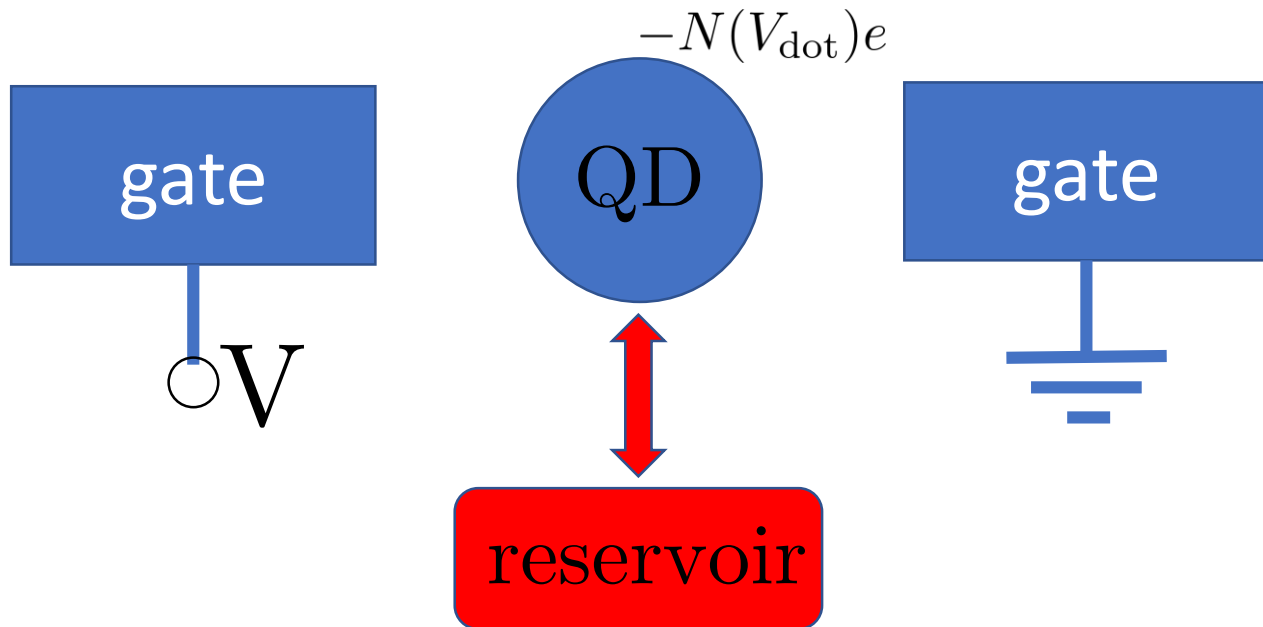
offset

$$I = C_{\text{diff}} \dot{V}$$

$$C_{\text{diff}} = \frac{dQ_1}{dV} = C_g$$

N is fixed

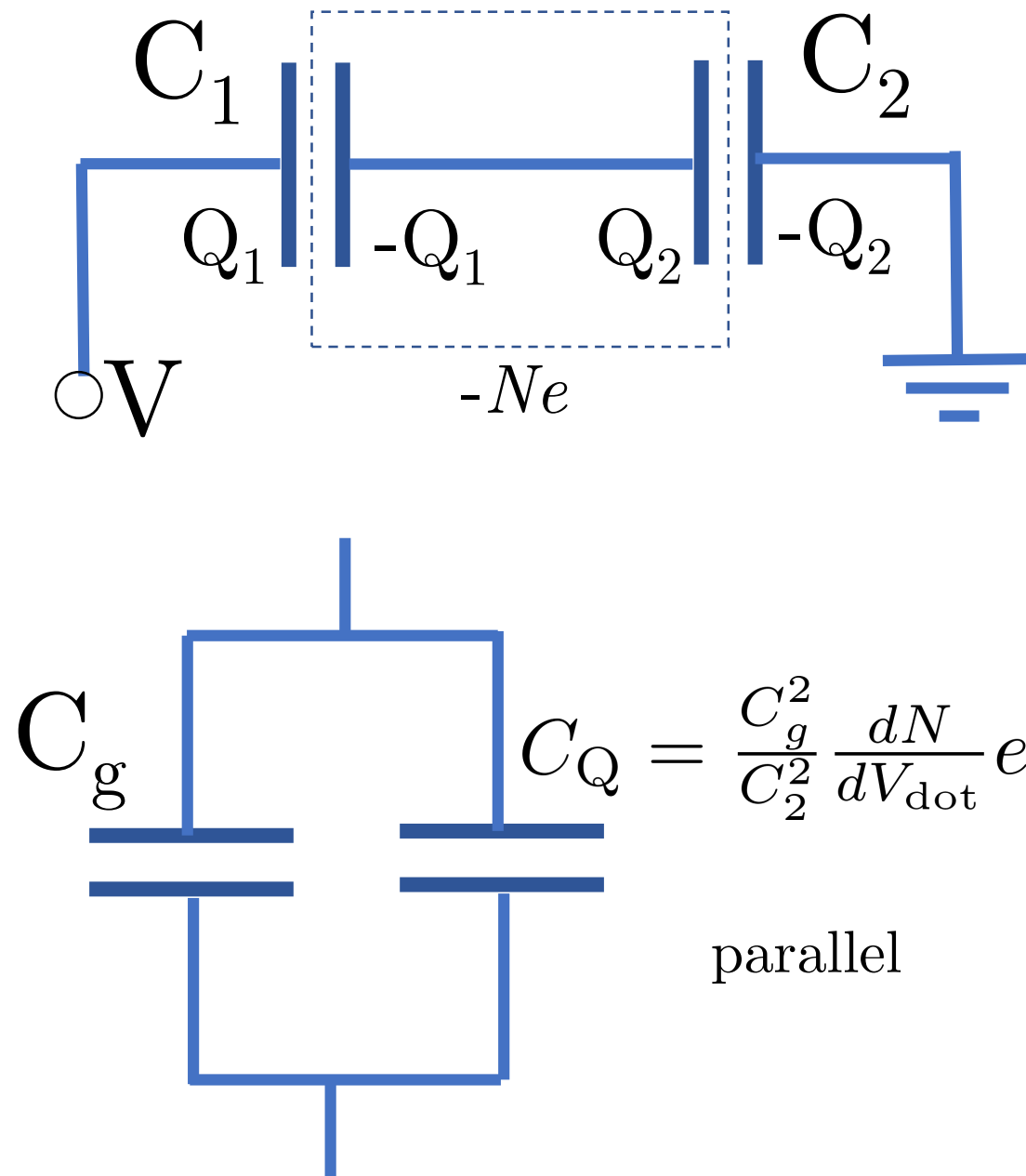
Quantum capacitance



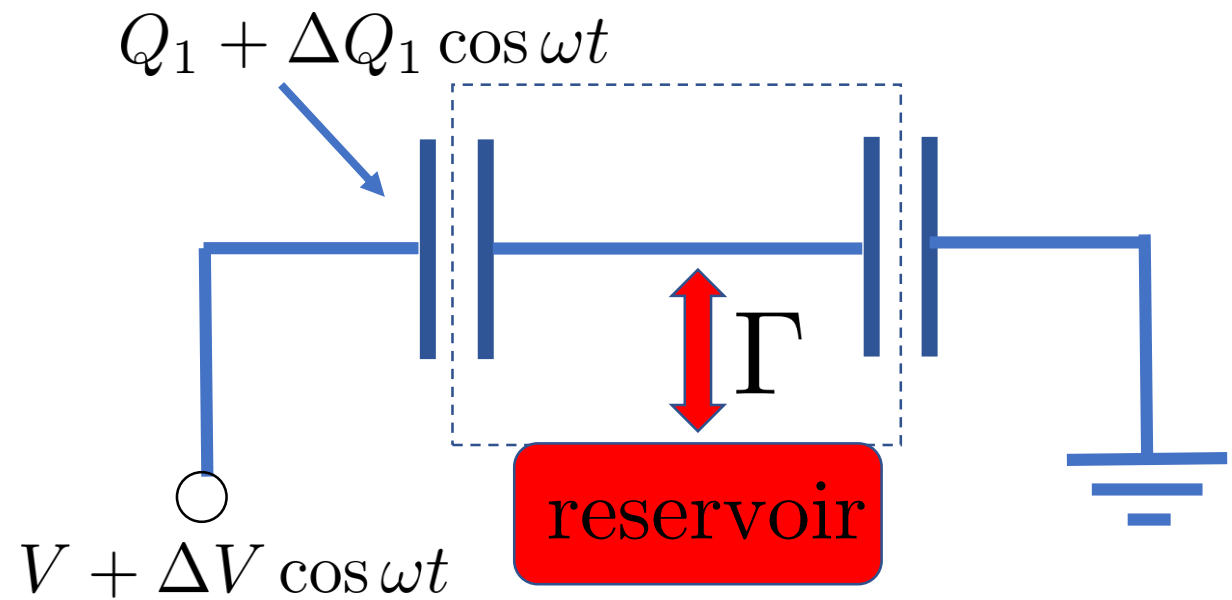
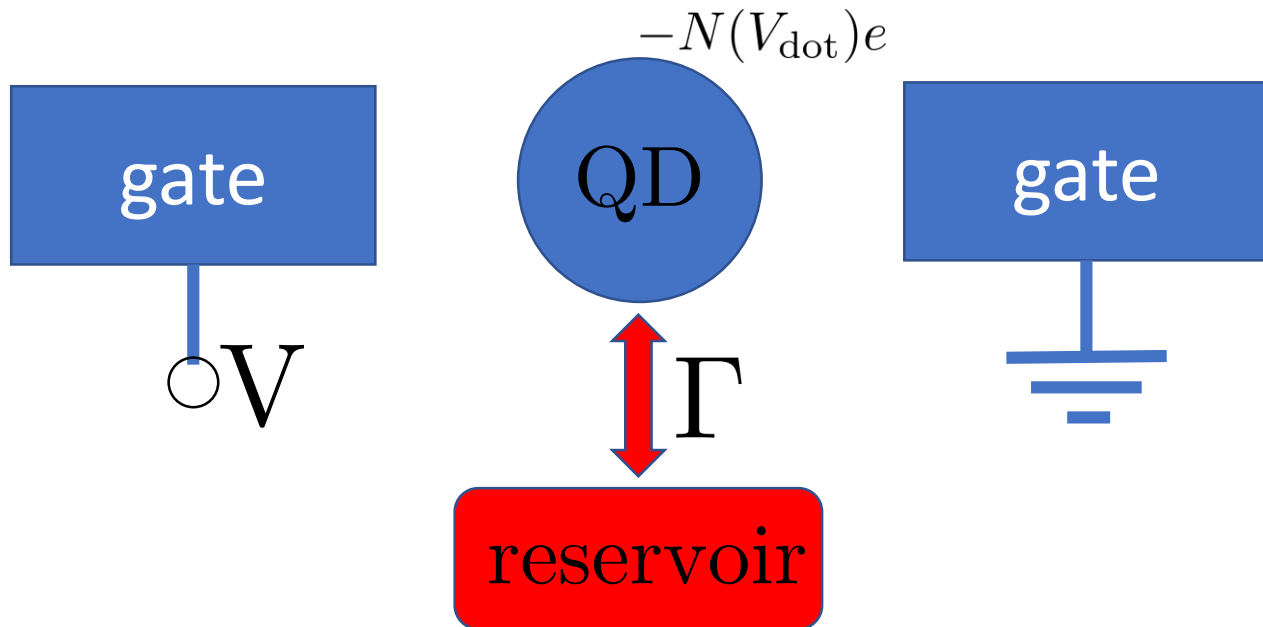
$$Q_1 = C_g V + \frac{C_g}{C_2} N e$$

$$C_{\text{diff}} = \frac{dQ_1}{dV} = C_g + \boxed{\frac{C_g}{C_2} \frac{dN}{dV} e}$$

C_Q : quantum capacitance



Quantum capacitance

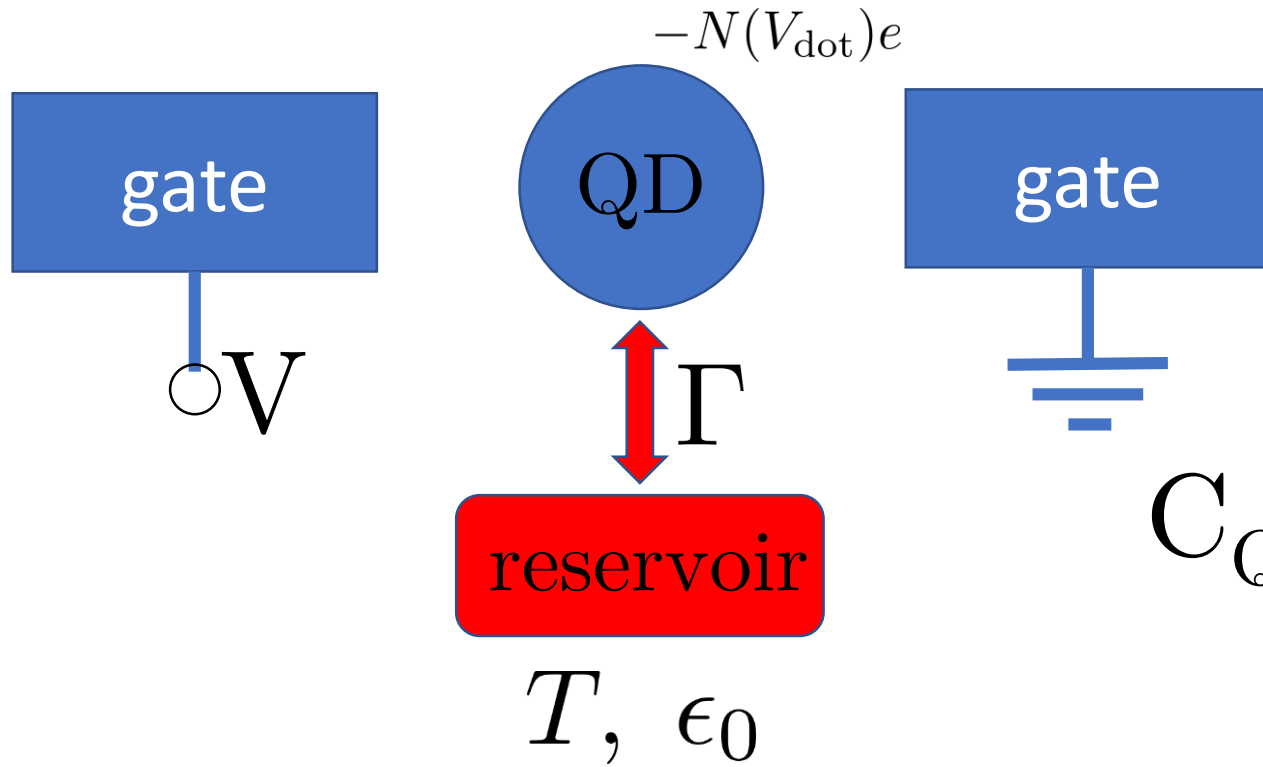


$$\Delta Q_1 = (C_g + C_Q(V)) \Delta V$$

$$\omega \gg \Gamma \rightarrow C_Q = 0$$

$$\omega \ll \Gamma \rightarrow \text{adiabatic}$$

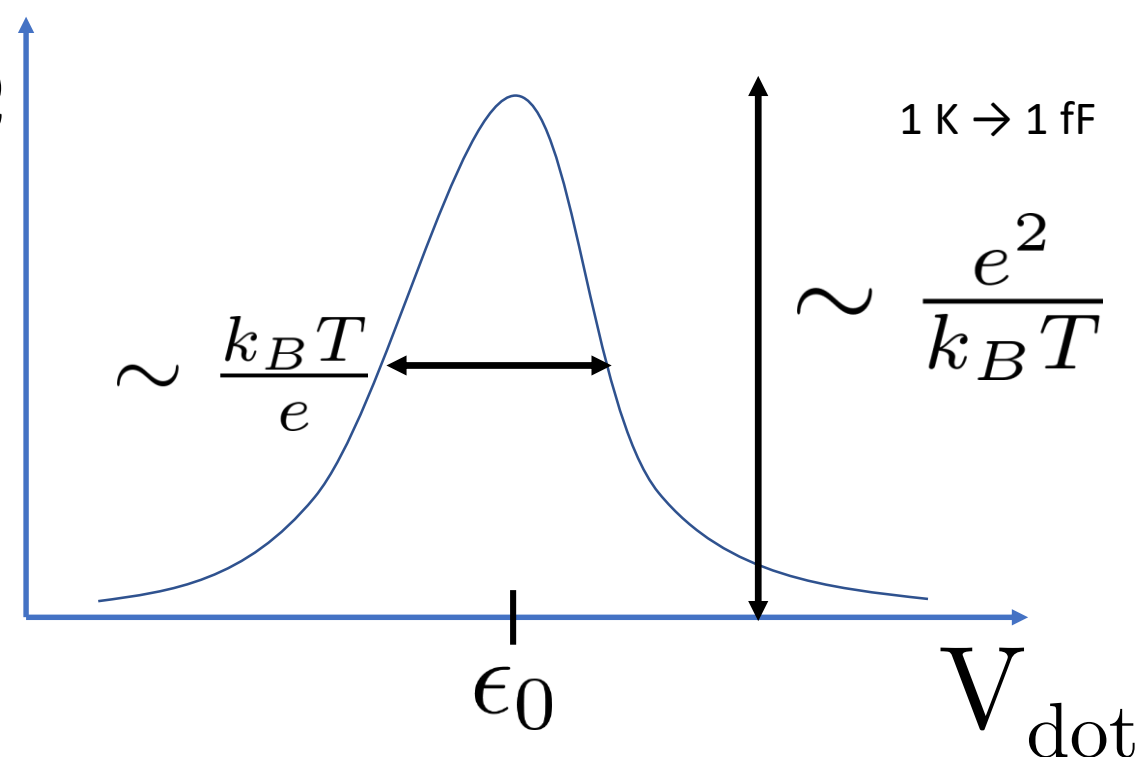
Quantumdot + Fermi-sea



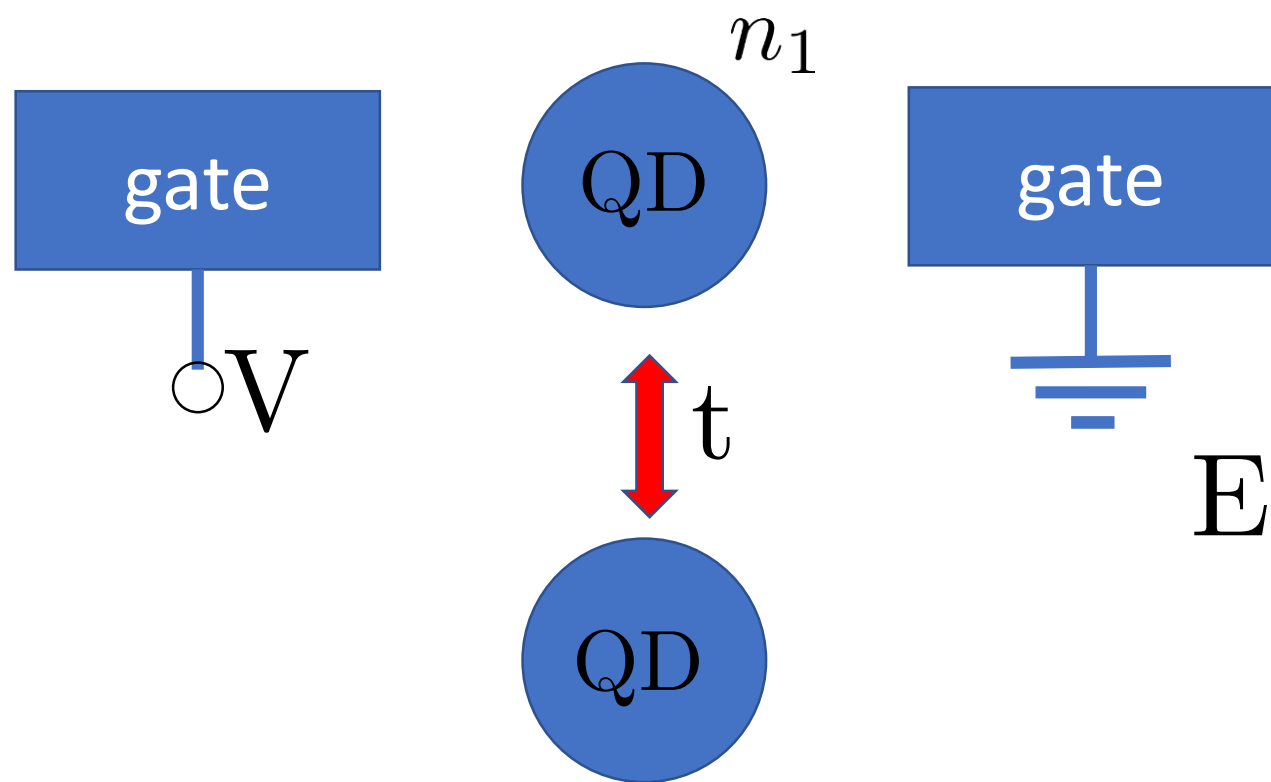
$$C_Q = \frac{C_g^2}{C_2^2} \frac{dN}{dV_{\text{dot}}} e$$

One level in the QD
Orbital energy = 0

$$N(V_{\text{dot}}) = \frac{1}{e^{\frac{eV_{\text{dot}} - \epsilon_0}{k_B T}} + 1}$$

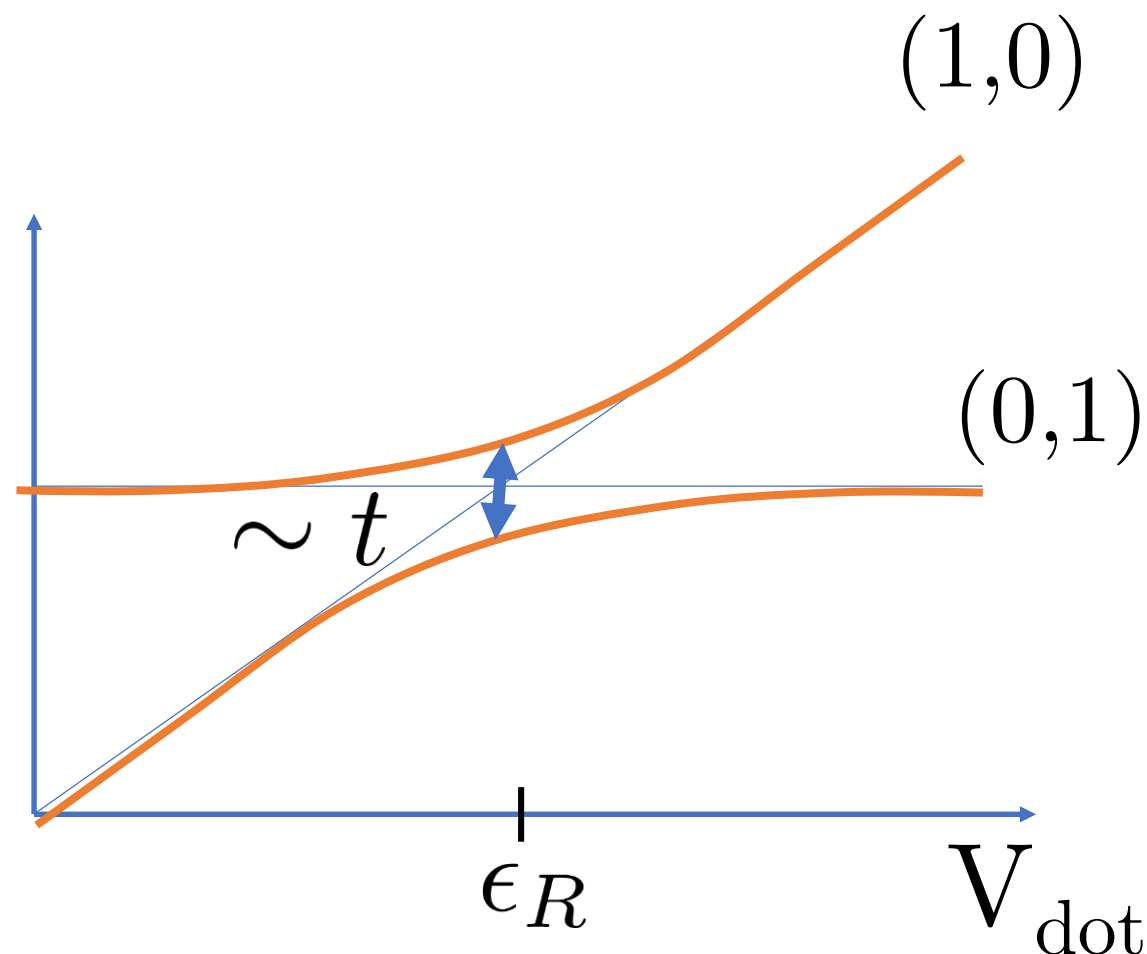


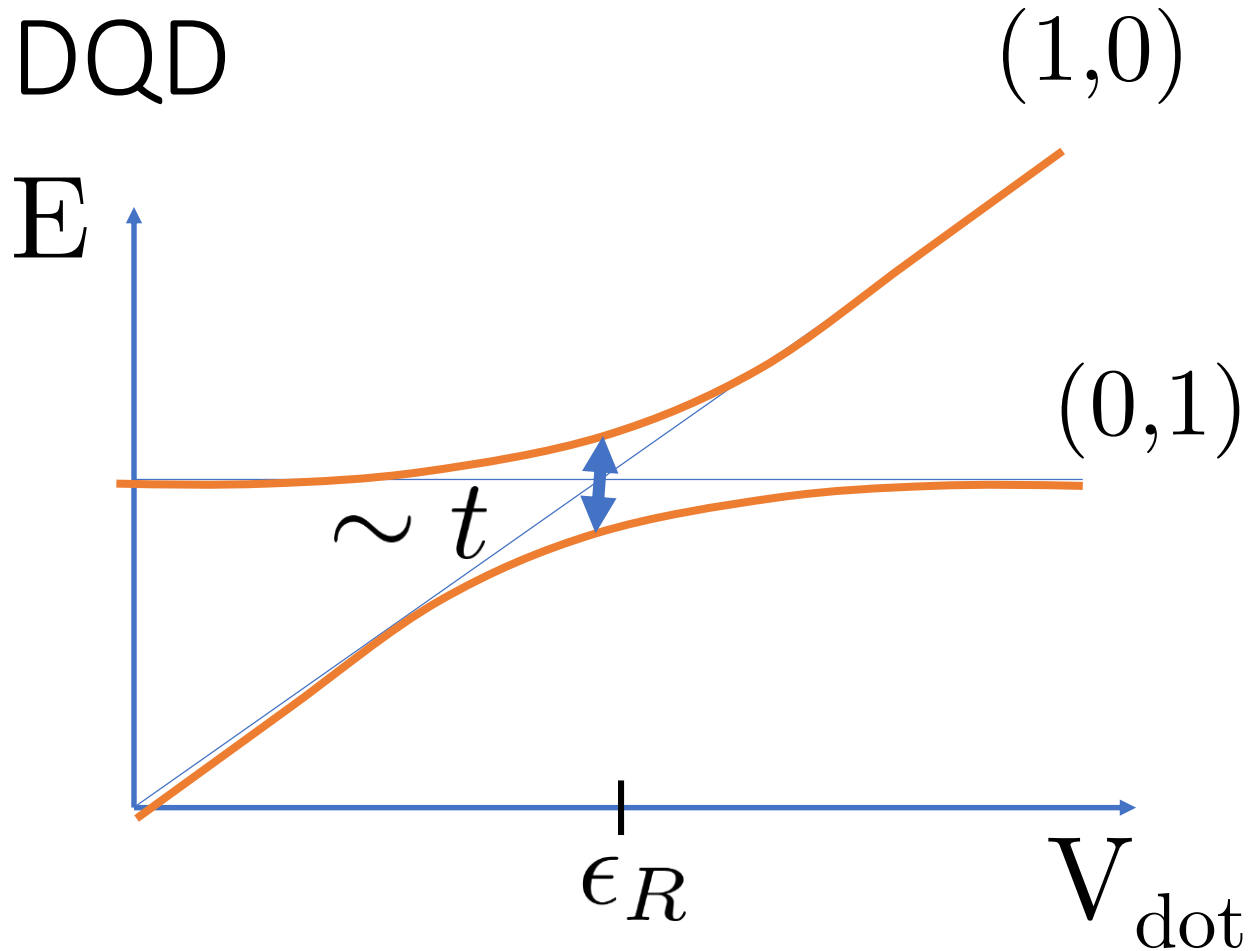
DQD



$$C_Q = \frac{C_g^2}{C_2^2} \frac{dn_1}{dV_{\text{dot}}} e$$

$$H = \begin{bmatrix} eV_{\text{dot}} & t \\ t & \epsilon_R \end{bmatrix}$$



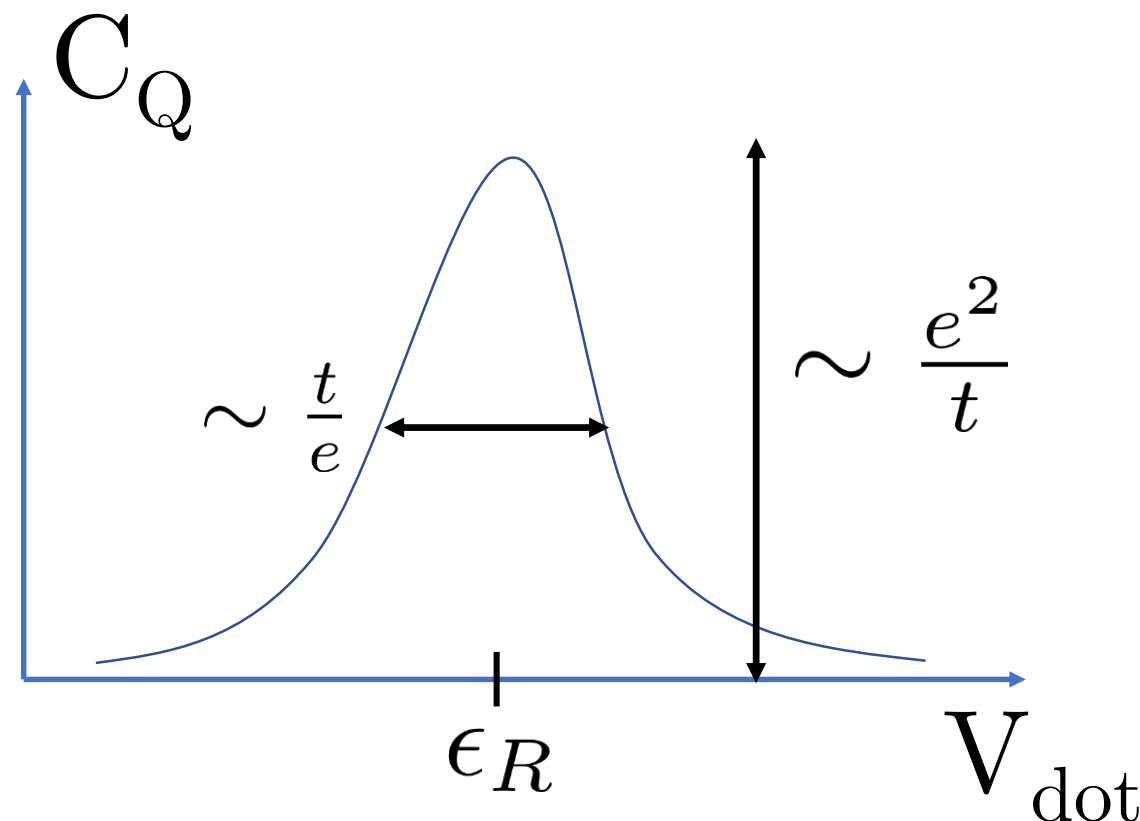


Adiabatically follow the ground state
no excitation, thermalization

$$C_Q = \frac{C_g^2}{C_2^2} \frac{2t^2 e^2}{(4t^2 + (eV_{\text{dot}} - \epsilon_R)^2)^{3/2}}$$

Excited state:

$$C_Q^{\text{ground}}(V) = -C_Q^{\text{excited}}(V)$$



DQD result

Mesoscopic admittance of a double quantum dot

Audrey Cottet, Christophe Mora and Takis Kontos

Physical Review B 83, 121311(R) (2011)

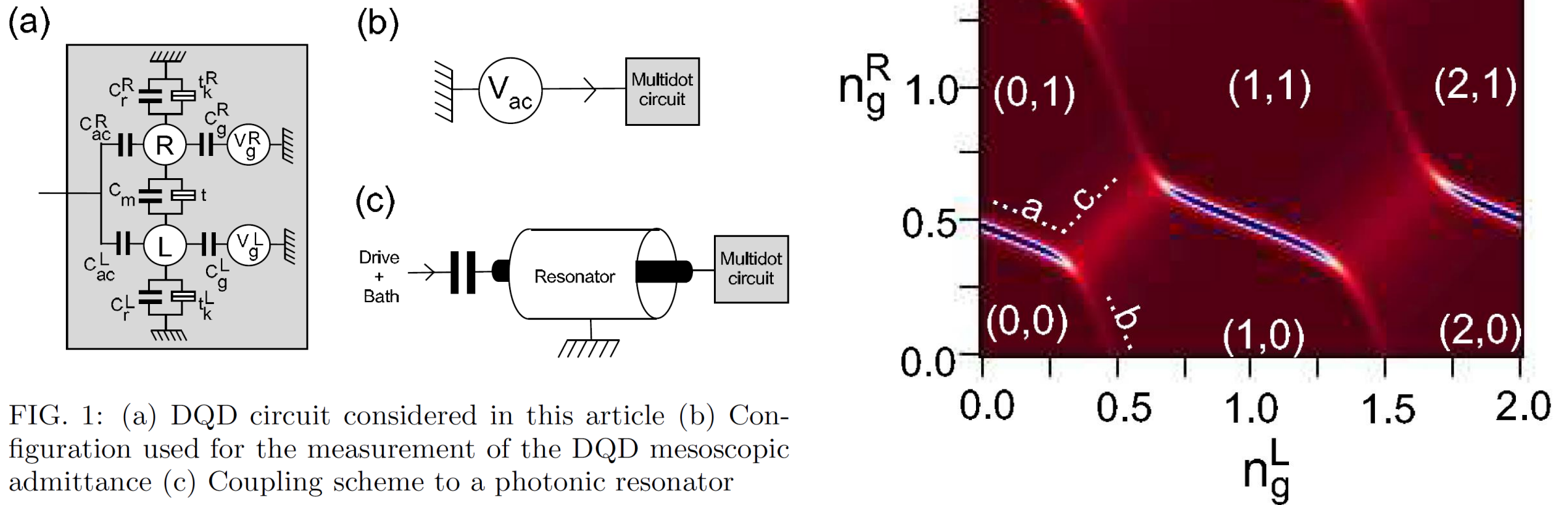


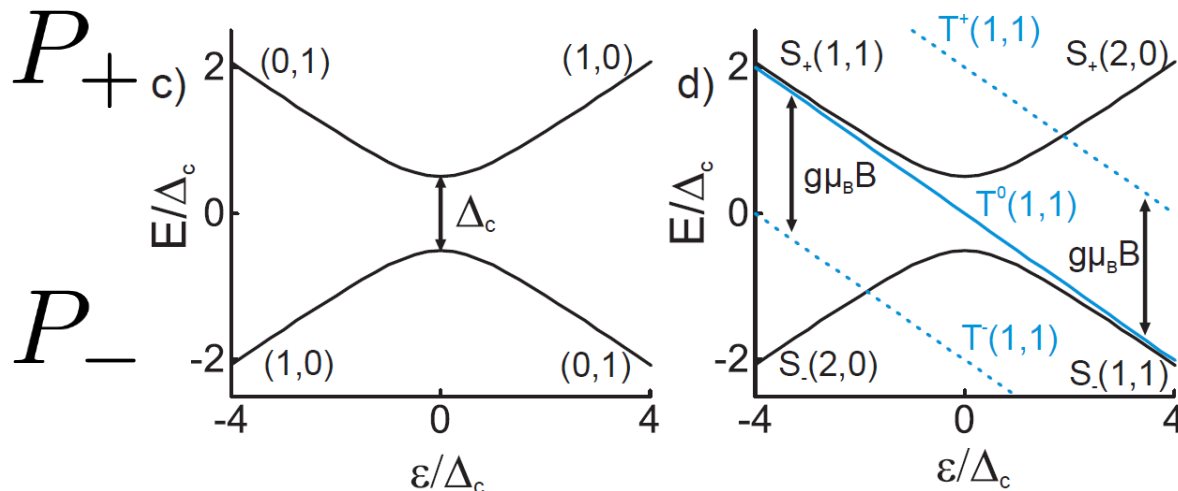
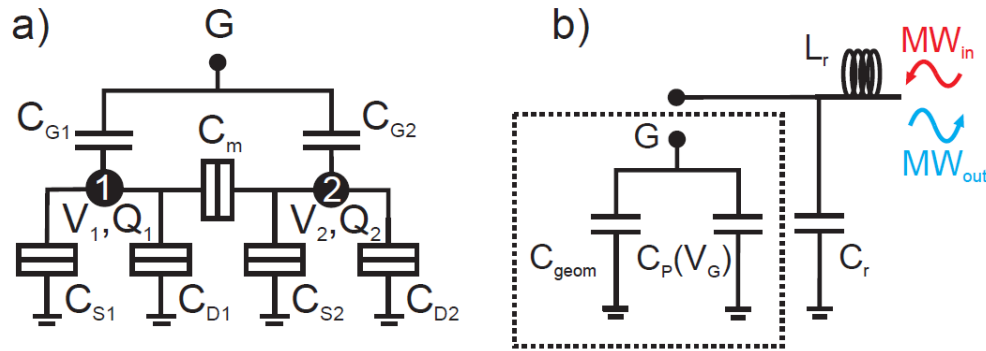
FIG. 1: (a) DQD circuit considered in this article (b) Configuration used for the measurement of the DQD mesoscopic admittance (c) Coupling scheme to a photonic resonator

Tunneling capacitance

Quantum and Tunnelling Capacitance in Charge and Spin Qubits

R. Mizuta, R. M. Otxoa, A. C. Betz, and M. F. Gonzalez-Zalba

Phys. Rev. B 95, 045414 (2017)



Slow-relaxation regime

thermal population constant

$$C_p = C_0(P_- - P_+) \frac{\Delta_c^3}{(\epsilon^2 + \Delta_c^2)^{3/2}}$$

Fast-relaxation regime

instantaneous thermal population

$$(P_- - P_+) = \tanh \left(\frac{\sqrt{(\epsilon^2 + \Delta_c^2)}}{2k_B T} \right)$$

Tunneling capacitance

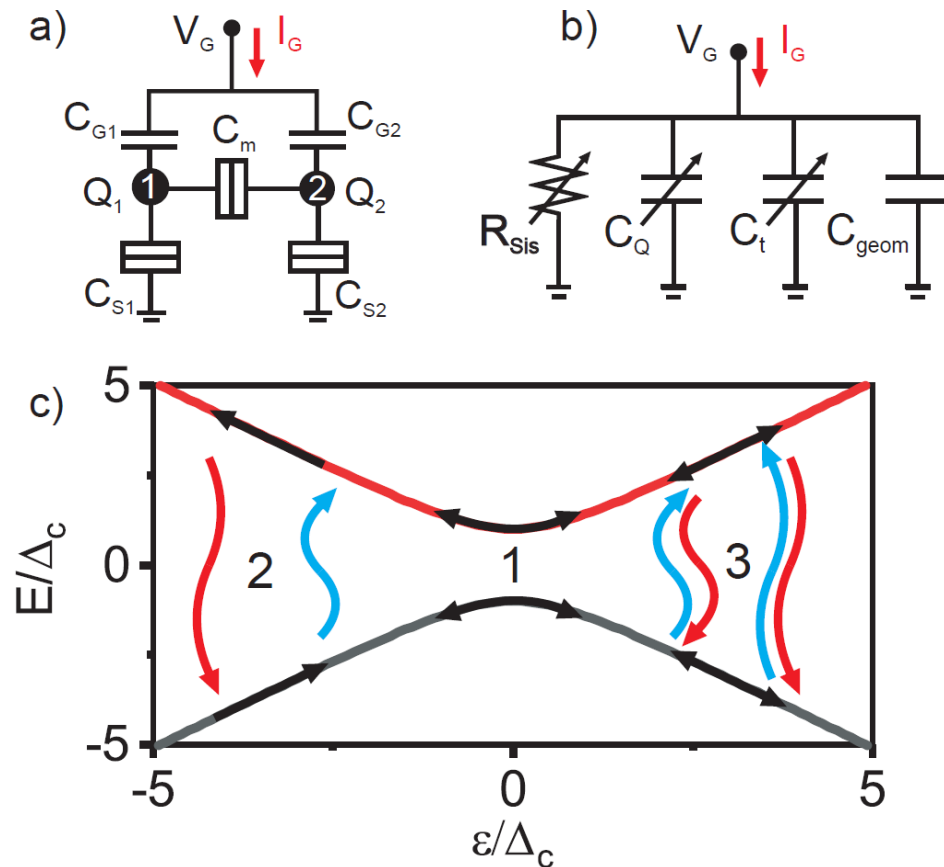
$$C_p = C_{\text{quantum}} + C_0 \frac{\epsilon \Delta_c}{\sqrt{\epsilon^2 + \Delta_c^2}} \frac{\partial(P_- - P_+)}{\partial \epsilon}$$

Sisyphus resistance

Small-signal equivalent circuit for double quantum dots at low-frequencies

M. Esterli,¹ R. M. Otxoa,^{1,2} and M. F. Gonzalez-Zalba¹

arXiv:1812.06056



characteristic rate of relaxation: γ

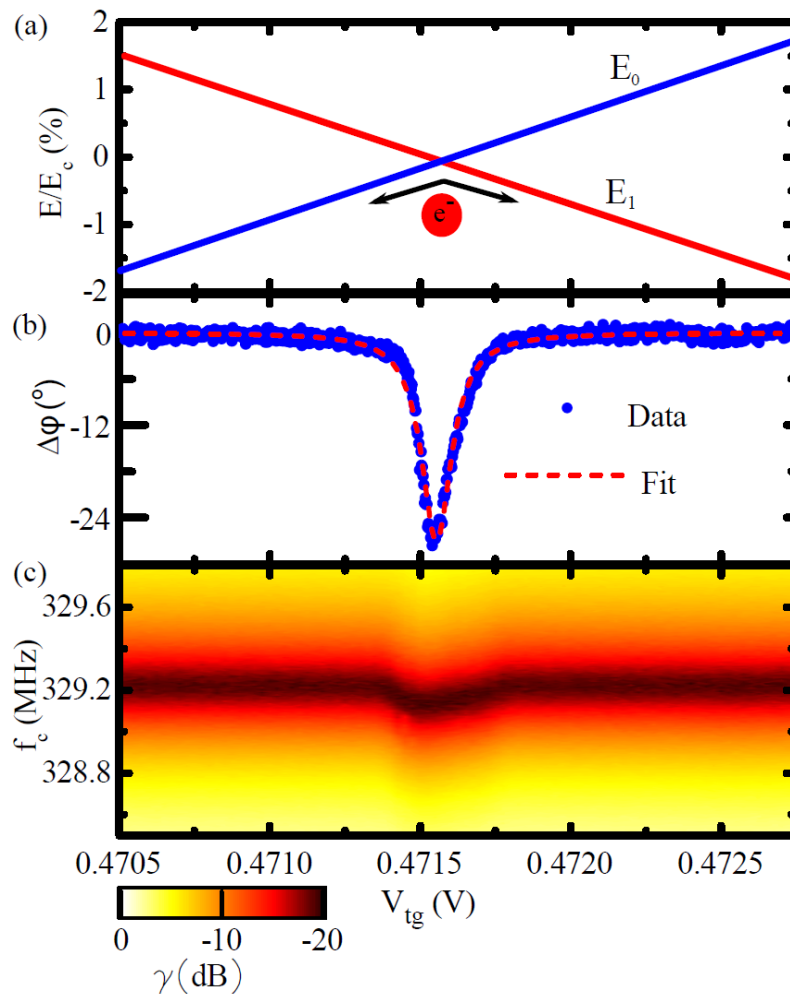
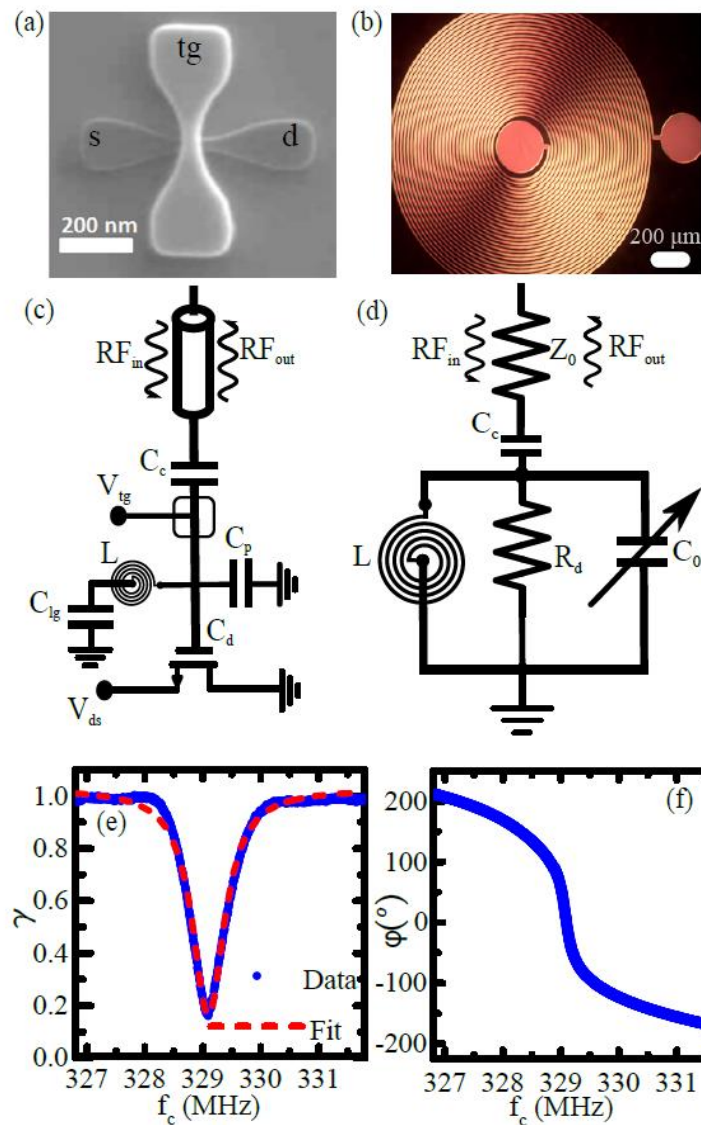
$$C_t = \frac{(e\alpha')^2}{2} \frac{1}{2k_B T} \left(\frac{\varepsilon_0}{\Delta E_0} \right)^2 \frac{\gamma^2}{\omega^2 + \gamma^2} \cosh^{-2}(\Delta E_0/2k_B T).$$

$$R_{Sis} = \frac{4R_Q}{\alpha'^2} \frac{k_B T}{h\gamma} \left(\frac{\Delta E_0}{\varepsilon_0} \right)^2 \frac{\omega^2 + \gamma^2}{\omega^2} \cosh^2(\Delta E_0/2k_B T).$$

Measuring quantum capacitance

Radio-frequency capacitive gate-based sensing

Intiaz Ahmed,^{1,*} James A. Haigh,² Simon Schaal,³ Sylvain Barraud,⁴ Yi Zhu,⁵ Chang-min Lee,⁵ Mario Amado,⁵ Jason W. A. Robinson,⁵ Alessandro Rossi,¹ John J. L. Morton,^{3,6} and M. Fernando Gonzalez-Zalba^{2,†}



$$f_0 = \frac{1}{2\pi\sqrt{LC}}$$

$$\Delta f = -f_0 \frac{\Delta C}{2C}$$

$$\Delta\phi = -2Q \frac{\Delta C}{C}$$